



BSP75GQ-13

60V SELF-PROTECTED LOW-SIDE IntelliFET MOSFET SWITCH

Product Summary

Continuous Drain-Source Voltage: VDS = 60V

On-State Resistance: 550mΩ

Nominal Load Current (V_{IN} = 5V): 1.4A

Clamping Energy: 550mJ

Description

The BSP75GQ-13 is a self-protected low-side IntelliFET[®] MOSFET. It features monolithic overtemperature, overcurrent, overvoltage (active clamp) and ESD protected logic-level functionality. It is intended as a general-purpose switch.

Applications

- Especially suited for loads with a high inrush current such as lamps and motors
- All types of resistive, inductive and capacitive loads in switching applications
- µC compatible power switches for 12V and 24V DC applications
- Automotive rated
- · Replaces electromechanical relays and discrete circuits
- Linear mode capabilities the current-limiting protection circuitry
 is designed to de-activate at low V_{DS} in order not to compromise
 the load current during normal operation. The maximum DC
 operating current is therefore determined by the thermal
 capability of the package/board combination, rather than by the
 protection circuitry.

Features and Benefits

- Short-Circuit Protection with Auto Restart
- Overvoltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- Load Dump Protection (Actively Protects Load)
- Logic-Level Input
- High Continuous Current Rating
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The BSP75GQ-13 is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

Package: SOT223

 Package Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

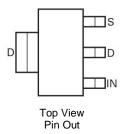
Terminals: Matte Tin Finish @3

Weight: 0.112 grams (Approximate)



Top View

SOT223



Note:

The tab is connected to the drain pin, and must be electrically isolated from the source pin. Connection of significant copper to the tab is recommended for best thermal performance.

Ordering Information (Note 4)

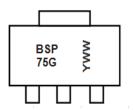
Part Number	Packago	Marking	Reel Size (inches)	Tape Width (mm)	Paci	king
Fait Number	Package	Warking	Reel Size (Iliches)	rape widin (ililii)	Qty.	Carrier
BSP75GQ-13	SOT223	BSP75G	13	12	4,000 Units	Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

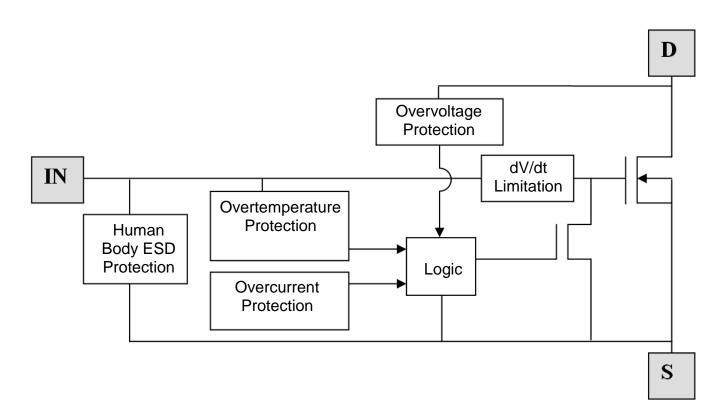


Marking Information



$$\begin{split} & \text{BSP75G} = \text{Product Type Marking Code} \\ & \text{YWW} = \text{Date Code Marking} \\ & \text{Y or } \overline{\text{Y}} = \text{Last Digit of Year (ex: 4 = 2024)} \\ & \text{WW or } \overline{\text{WW}} = \text{Week Code (01 to 53)} \end{split}$$

Functional Block Diagram





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise stated.)

Parameter	Symbol	Value	Unit
Continuous Drain-Source Voltage	V _{DS}	60	V
Drain-Source Voltage for Short-Circuit Protection, V _{IN} = 5V	VDS(SC)	36	V
Continuous Input Voltage	Vin	-0.2 to +10	V
Peak Input Voltage	VIN	-0.2 to +20	V
Operating Temperature Range	TJ	-40 to +150	ů
Storage Temperature Range	T _{STG}	-55 to +150	°C
Power Dissipation at T _A = +25°C (Note 5)	P _D	2.5	W
Continuous Drain Current @ V _{IN} = 10V; T _A = +25°C (Note 5)	I _D	1.6	Α
Continuous Drain Current @ V _{IN} = 5V; T _A = +25°C (Note 5)	ID	1.4	Α
Pulsed Drain Current @ V _{IN} = 10V	I _{DM}	5	Α
Continuous Source Current (Body Diode) (Note 5)	Is	3	Α
Pulsed Source Current (Body Diode)	Is	5	Α
Unclamped Single Pulse Inductive Energy	Eas	550	mJ
Load Dump Protection	VLOAD_DUMP	80	V
Electrostatic Discharge (Human Body Model)	V _{ESD}	4000	V
DIN Humidity Category, DIN 40 040	_	E	_
IEC Climatic Category, DIN IEC 68-1	_	40/150/56	

Thermal Resistance

Characteristic	Symbol	Value	Unit
Junction to Ambient (Note 5)	$R_{\theta JA}$	50	°C/W
Junction to Ambient (Note 6)	Reja	24	°C/W
Junction to Ambient (Note 7)	Reja	208	°C/W

Notes:

- 5. For a device surface-mounted on 37mm x 37mm x 1.6mm FR-4 board with a high coverage of single sided 2oz weight copper.
- 6. For a device surface-mounted on FR-4 board and measured at t ≤ 10s.7. For a device mounted on FR-4 board with the minimum copper required for electrical connections.



Electrical Characteristics (@T_A = +25°C, unless otherwise stated.)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Static Characteristics						
Drain-Source Clamp Voltage	V _{DS(AZ)}	60	70	75	V	I _D = 10mA
Off-State Drain Current	IDSS	_	0.1	3	μA	V _{DS} = 12V, V _{IN} = 0V
Off-State Drain Current	IDSS	_	3	15	μΑ	V _{DS} = 32V, V _{IN} = 0V
Input Threshold Voltage (Note 8)	VIN(TH)	1	2.1	_	V	V _{DS} = V _{GS} , I _D = 1mA
Input Current	lın	_	0.7	1.2	mA	V _{IN} = 5V
Input Current	I _{IN}	_	1.5	2.7	mA	V _{IN} = 7V
Input Current	I _{IN}	_	4	7	mA	V _{IN} = 10V
Static Drain-Source On-State Resistance	RDS(ON)	_	520	675	mΩ	$V_{IN} = 5V, I_D = 0.7A$
Static Drain-Source On-State Resistance	RDS(ON)	_	385	550	mΩ	V _{IN} = 10V, I _D = 0.7A
Current Limit (Note 9)	I _{D(LIM)}	0.7	1.1	1.75	Α	$V_{IN} = 5V$, $V_{DS} > 5V$
Current Limit (Note 9)	I _{D(LIM)}	2	3	4	Α	V _{IN} = 10V, V _{DS} > 5V
Dynamic Characteristics						
Turn-On Time (V _{IN} to 90% I _D)	ton	_	2.2	_	μs	$R_L = 22\Omega$, $V_{IN} = 0$ to 10V, $V_{DD} = 12V$
Turn-Off Time (V _{IN} to 90% I _D)	toff	_	13	_	μs	$R_L = 22\Omega$, $V_{IN} = 10V$ to $0V$, $V_{DD} = 12V$
Slew Rate On (70 to 50% V _{DD})	-dV _{DS} /dto _N	_	10	_	V/µs	$R_L = 22\Omega$, $V_{IN} = 0$ to 10V, $V_{DD} = 12V$
Slew Rate Off (50 to 70% V _{DD})	dV _{DS} /dto _N	_	3.2	_	V/µs	$R_L = 22\Omega$, $V_{IN} = 10V$ to $0V$, $V_{DD} = 12V$
Protection Functions (Note 10)						
Minimum Input Voltage for Overtemperature Protection	VPROT	4.5	_	_	V	_
Thermal Overload Trip Temperature	T_{JT}	+150	+175	_	°C	_
Thermal Hysteresis	_	_	+10	_	°C	_
Unclamped Single Pulse Inductive Energy T _J = +25°C	Eas	550	-	-	mJ	I _D (I _{SO}) = 0.7A, V _{DD} = 32V
Unclamped Single Pulse Inductive Energy T _J = +150°C	E _{AS}	200	_	_	mJ	I _{D(ISO)} = 0.7A, V _{DD} = 32V
Inverse Diode						
Source-Drain Voltage	VsD	_	_	1	V	V _{IN} = 0V, -I _D = 1.4A

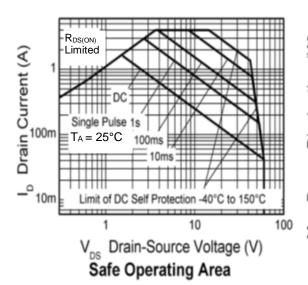
Notes:

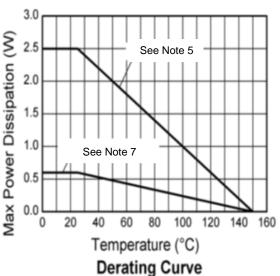
^{8.} Protection features may operate outside spec for V_{IN} < 4.5V.

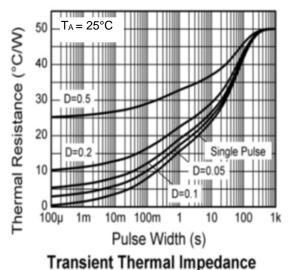
^{9.} The drain current is limited to a reduced value when V_{DS} exceeds a safe level.
10. Integrated protection functions are designed to prevent IC destruction under fault conditions described in the datasheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous, repetitive operation.

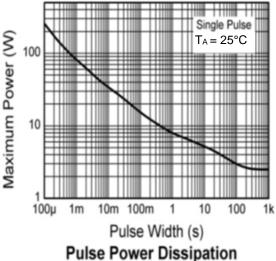


Typical Characteristics



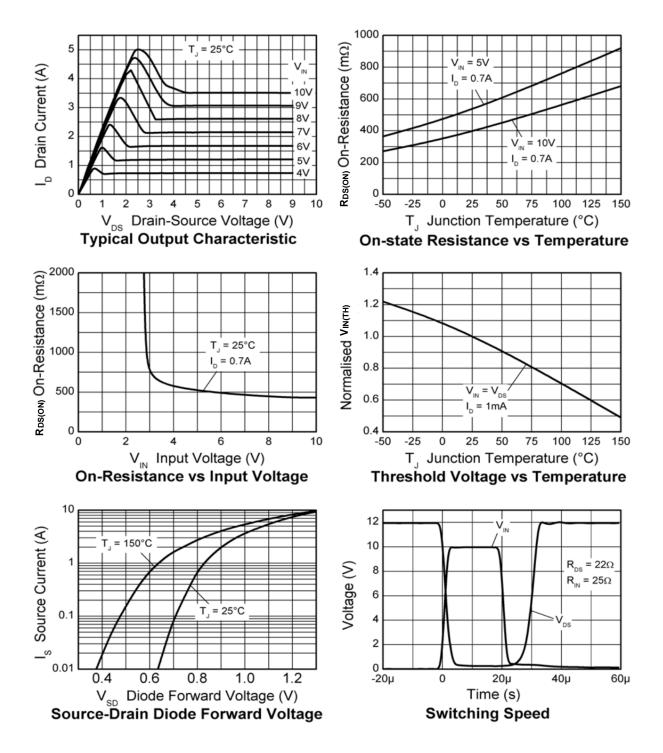








Typical Characteristics (continued)

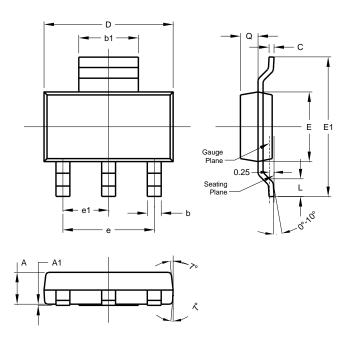




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

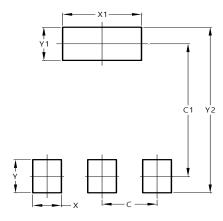


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
C	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
V2	8.00



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